



10BQ200 SCHOTTKY RECTIFIER

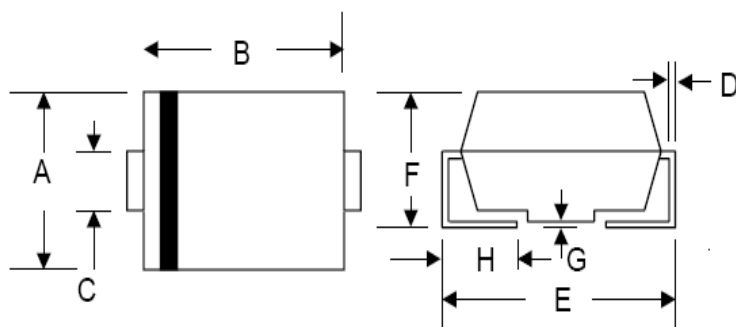
Applications:

- Disk Drives
- Switching power supply
- Redundant power subsystems
- Converters
- Free-Wheeling diodes
- Reverse battery protection
- Battery Charging

Features:

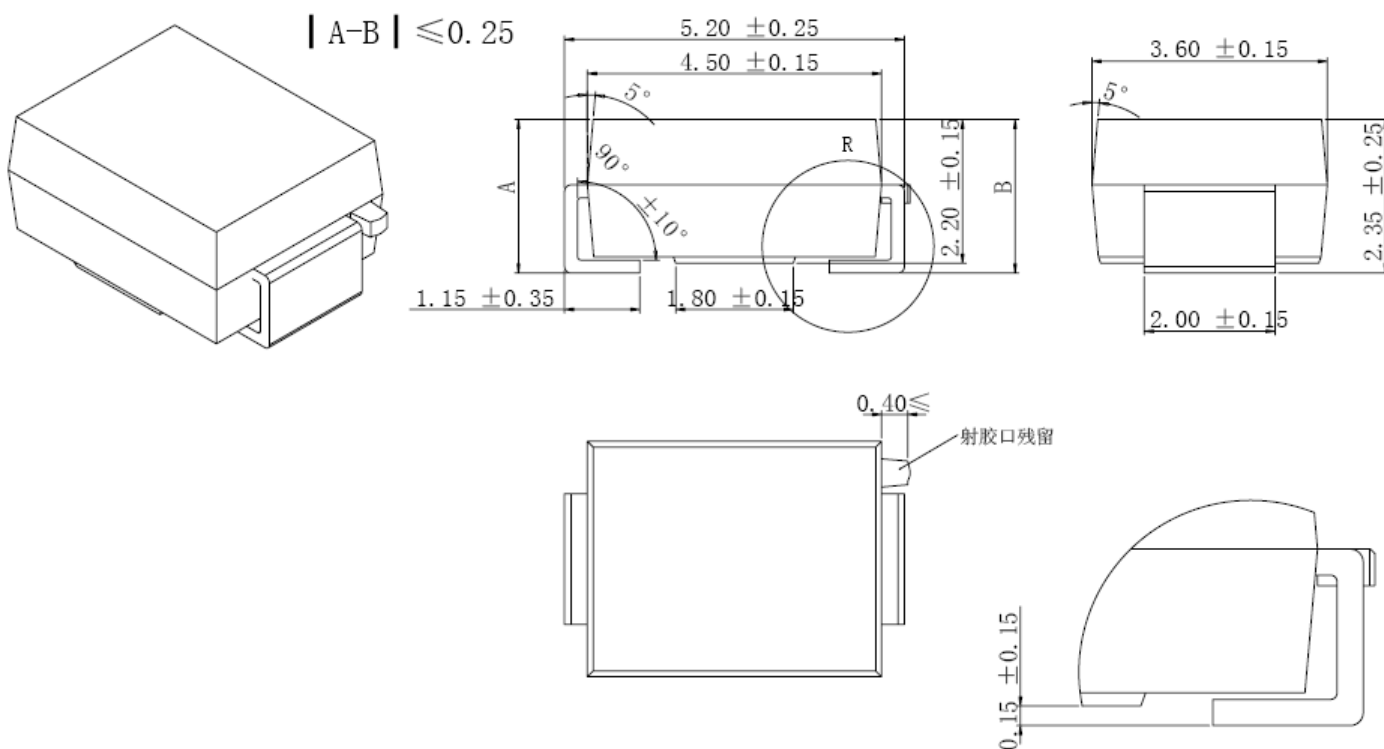
- Small foot print, surface moutable
- Low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Mechanical Dimensions: In mm



SMB/DO-214AA				
Dim	Min	Max	Min	Max
A	3.30	3.94	0.130	0.155
B	4.06	4.70	0.160	0.185
C	1.91	2.11	0.075	0.083
D	0.152	0.305	0.006	0.012
E	5.08	5.59	0.2	0.220
F	2.13	2.44	0.084	0.096
G	0.051	0.203	0.002	0.008
H	0.76	1.27	0.029	0.05
		in mm		In inch

OPTION 1



OPTION 2(JK)

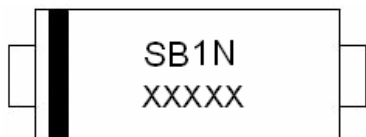
SMB



Technical Data
Data Sheet N0648, Rev. -

Green Products

Marking Diagram:



Where XXXXX is YYWWL

SB1N = Part Name
YY = Year
WW = Week
L = Lot Number

Cautions: Molding resin
Epoxy resin UL:94V-0

Ordering Information:

Device	Package	Shipping
10BQ200	SMB (Pb-Free)	3000pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V_{RWM}	-	200	V
Max. Average Forward Current	$I_{F(AV)}$	50% duty cycle @ $T_L = 105^\circ\text{C}$, rectangular wave form On PC board 9mm^2 island	1.0	A
Max. Peak One Cycle Non-Repetitive Surge Current (per leg)	I_{FSM}	10 ms, half Sine pulse	20	A



Electrical Characteristics:

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop*	V_{F1}	@ 1 A, Pulse, $T_J = 25\text{ }^{\circ}\text{C}$	0.92	V
	V_{F2}	@ 1 A, Pulse, $T_J = 125\text{ }^{\circ}\text{C}$	0.76	V
Max. Reverse Current *	I_{R1}	@ $V_R = \text{Rated } V_R$, Pulse, $T_J = 25\text{ }^{\circ}\text{C}$	0.5	mA
	I_{R2}	@ $V_R = \text{Rated } V_R$, Pulse, $T_J = 125\text{ }^{\circ}\text{C}$	1.0	mA
Max. Junction Capacitance	C_T	@ $V_R = 5\text{ V}$, $T_C = 25\text{ }^{\circ}\text{C}$ $f_{SIG} = 1\text{ MHz}$	20	PF
Typical Series Inductance	L_S	Measured lead to lead 5 mm from package body	2.0	nH
Max. Voltage Rate of Change	dv/dt	-	10,000	V/ μs

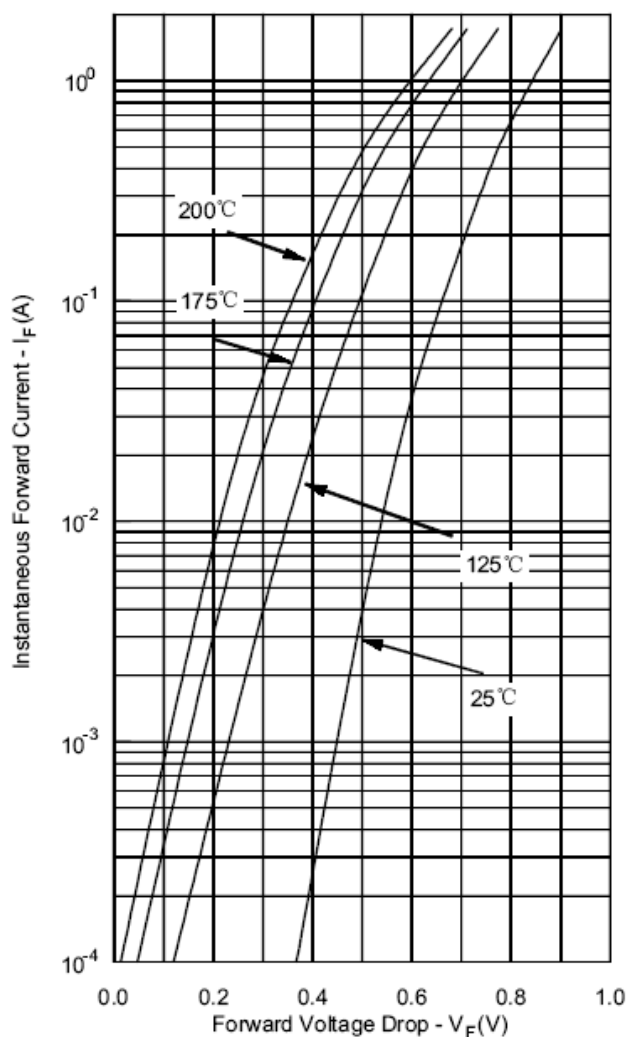
* Pulse Width < 300 μs , Duty Cycle < 2%

Thermal-Mechanical Specifications:

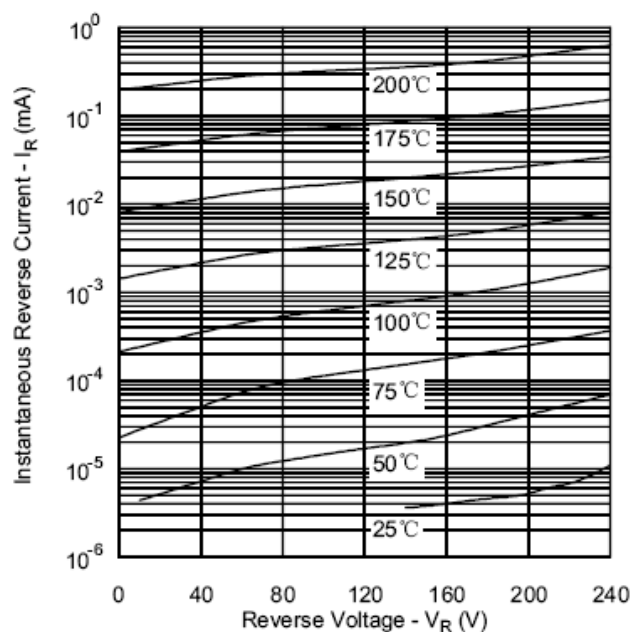
Characteristics	Symbol	Condition	Specification	Units
Max. Junction Temperature	T_J	-	-55 to +175	$^{\circ}\text{C}$
Max. Storage Temperature	T_{stg}	-	-55 to +175	$^{\circ}\text{C}$
Maximum Thermal Resistance Junction to Case	$R_{\theta JA}$	DC operation	140	$^{\circ}\text{C/W}$
Approximate Weight	wt	-	0.68	g
Case Style	SMB			



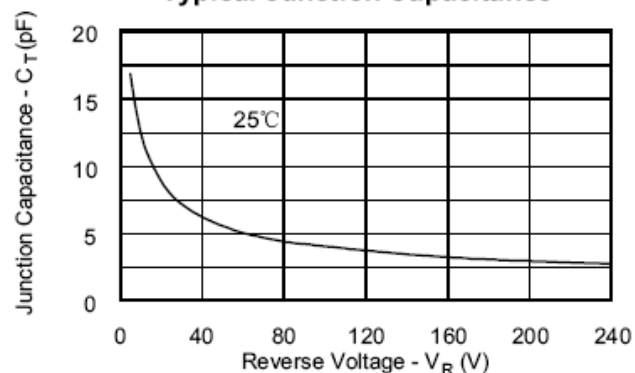
Typical Forward Characteristics



Typical Reverse Characteristics



Typical Junction Capacitance





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